



#### **DUAL P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON) max</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C	
-30V	45mΩ @ V <sub>GS</sub> = -10V	-6.9A	
	65mΩ @ V <sub>GS</sub> = -4.5V	-5.1A	

## **Description**

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Power Management Functions
- Backlighting
- DC-DC Converters

# S1 1 8 D1 7 D1 S2 3 6 D2 Top View Internal Schematic

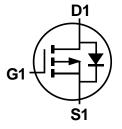
#### **Features**

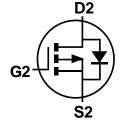
- Dual P-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Mechanical Data**

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208@3
- Weight: 0.072g (Approximate)

SO-8





P-Channel MOSFET

P-Channel MOSFET

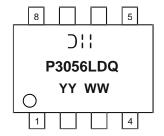
#### **Ordering Information** (Note 5)

Part Number	Case	Packaging
DMP3056LSDQ-13	SO-8	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/product-compliance-definitions/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

#### **Marking Information**



⊃!! = Manufacturer's Marking
P3056LDQ = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 17 = 2017)
WW = Week (01 to 53)



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Chara	cteristic		Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Drain Current (Note 6)	Steady State	$T_A = +25$ °C $T_A = +70$ °C	ID	-6.9 -5.8	А
Pulsed Drain Current (Note 7)			I <sub>DM</sub>	-24	Α

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	$P_{D}$	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ hetaJA}$	50	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

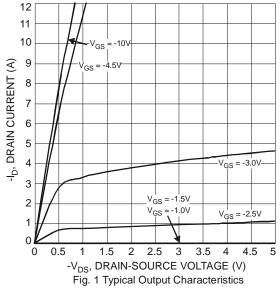
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)				•		•
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ű	IGSS			±800	IIA	$V_{GS} = \pm 25V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1	-1.7	-2.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance	Proven	_	_	45	mΩ	$V_{GS} = -10V, I_D = -6.0A$
Static Brain Gource On Resistance	R <sub>DS(ON)</sub>		_	65	1115.2	$V_{GS} = -4.5V$ , $I_D = -5.0A$
Forward Transconductance	<b>g</b> fs	_	8	_	S	$V_{DS} = -10V, I_D = -5.3A$
Diode Forward Voltage (Note 8)	$V_{SD}$	-0.5	_	-1.2	V	$V_{GS} = 0V, I_{S} = -1.7A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C <sub>iss</sub>	_	722		pF	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
Output Capacitance	Coss	_	114	_	pF	$V_{DS} = -25V, V_{GS} = 0V$ - f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	92	_	pF	1 - 1.01/11/12
Gate Resistance	R <sub>G</sub>	_	3.3	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ f = 1.0MHz
SWITCHING CHARACTERISTICS						
Total Gate Charge	$Q_{G}$	_	6.8	_	nC	$V_{DS} = -15V, V_{GS} = -4.5V,$ $I_{D} = -6A$
·	$Q_{G}$	_	13.7	_		V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -6A
Gate-Source Charge	Q <sub>GS</sub>	_	1.6	_	nC	
Gate-Drain Charge	$Q_{GD}$	_	4.2			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	6.4	_		$V_{DS} = -15V$ , $V_{GS} = -10V$ , $I_{D} = -1A$ , $R_{G} = 6.0\Omega$
Rise Time	t <sub>R</sub>	_	5.3	_		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	26.5	_	ns	
Fall Time	t <sub>F</sub>	_	14.7	_		

Notes: 6. Device mounted on 2 oz. 1" x 1" Copper pads on 2" x 2" FR-4 PCB.

Pulse width ≤10μS, Duty Cycle ≤1%.
 Short duration pulse test used to minimize self-heating effect.





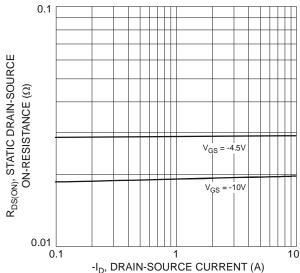
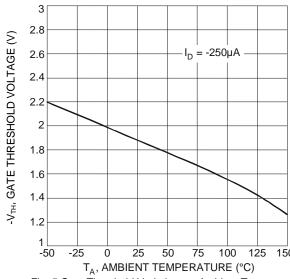
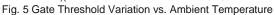
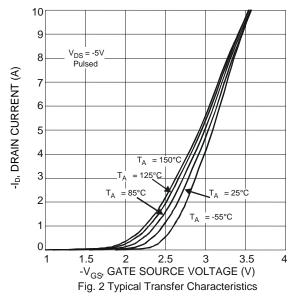


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage







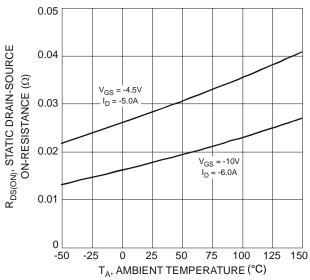
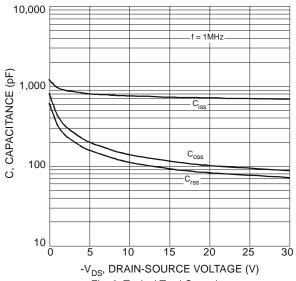
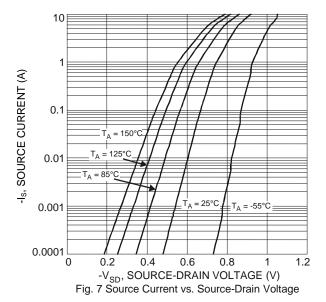


Fig. 4 Static Drain-Source On-Resistance vs. Ambient Temperature





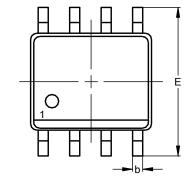


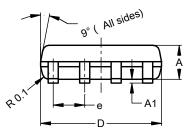


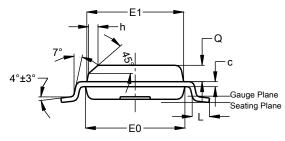
# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

**SO-8** 





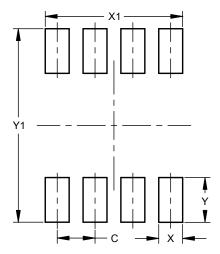


SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h	-		0.35		
L	0.62	0.82	0.72		
Q	0.60	0.70	0.65		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)		
С	1.27		
Х	0.802		
X1	4.612		
Υ	1.505		
Y1	6.50		



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